



PH3330L

N-channel TrenchMOS logic level FET

Rev. 01 — 1 February 2006

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology.

1.2 Features

- Optimized for use in DC-to-DC converters
- Logic level compatible
- Very low switching and conduction losses
- Lead-free package

1.3 Applications

- DC-to-DC converters
- Voltage regulators
- Switched-mode power supplies
- Notebook computers

1.4 Quick reference data

- $V_{DS} \leq 30\text{ V}$
- $R_{DS(on)} \leq 3.3\text{ m}\Omega$
- $I_D \leq 100\text{ A}$
- $Q_{GD} = 6.9\text{ nC (typ)}$

2. Pinning information

Table 1: Pinning

Pin	Description	Simplified outline	Symbol
1, 2, 3	source (S)		
4	gate (G)		
mb	mounting base; connected to drain (D)		

SOT669 (LPAK)

3. Ordering information

Table 2: Ordering information

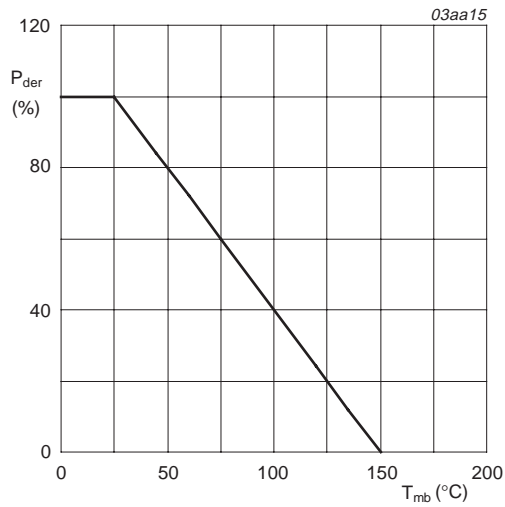
Type number	Package		Version
	Name	Description	
PH3330L	LFAK	plastic single-ended surface mounted package (LFAK); 4 leads	SOT669

4. Limiting values

Table 3: Limiting values

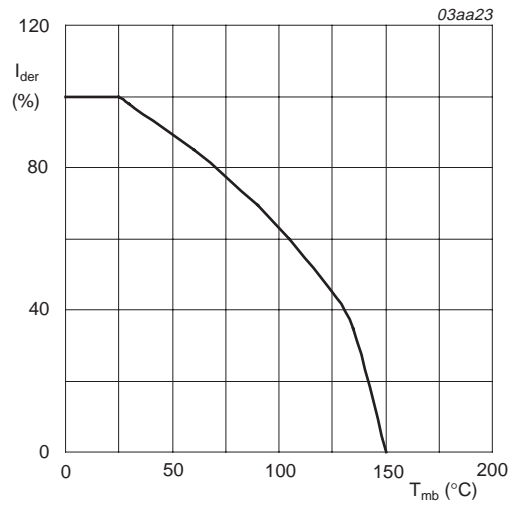
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-	± 20	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 2 and 3	-	100	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 2	-	54.2	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 3	-	300	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 1	-	62.5	W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		-55	+150	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	52	A
I_{SM}	peak source current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	208	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 70\text{ A}$; $t_p = 0.15\text{ ms}$; $V_{DS} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; starting at $T_j = 25\text{ °C}$	-	245	mJ



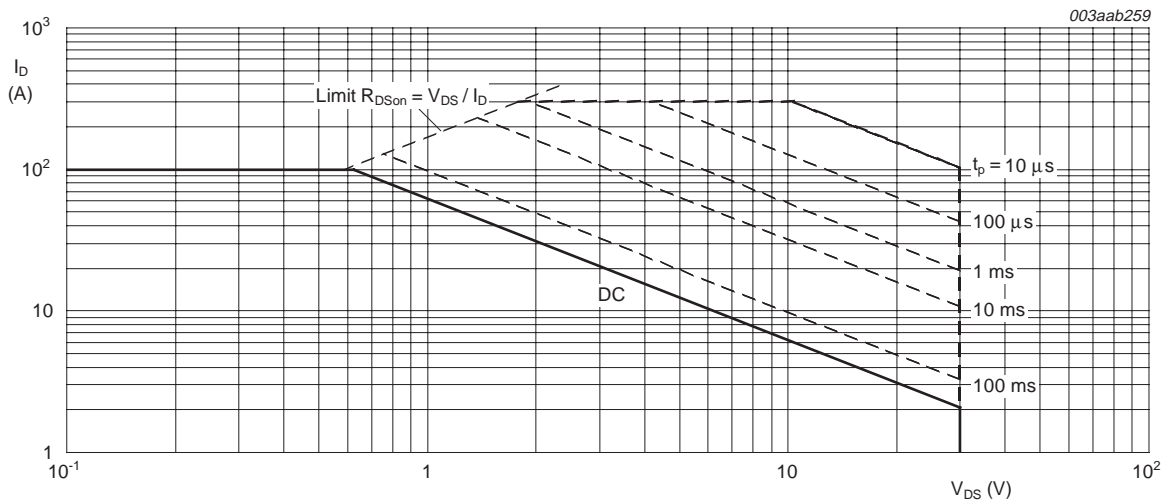
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2	K/W

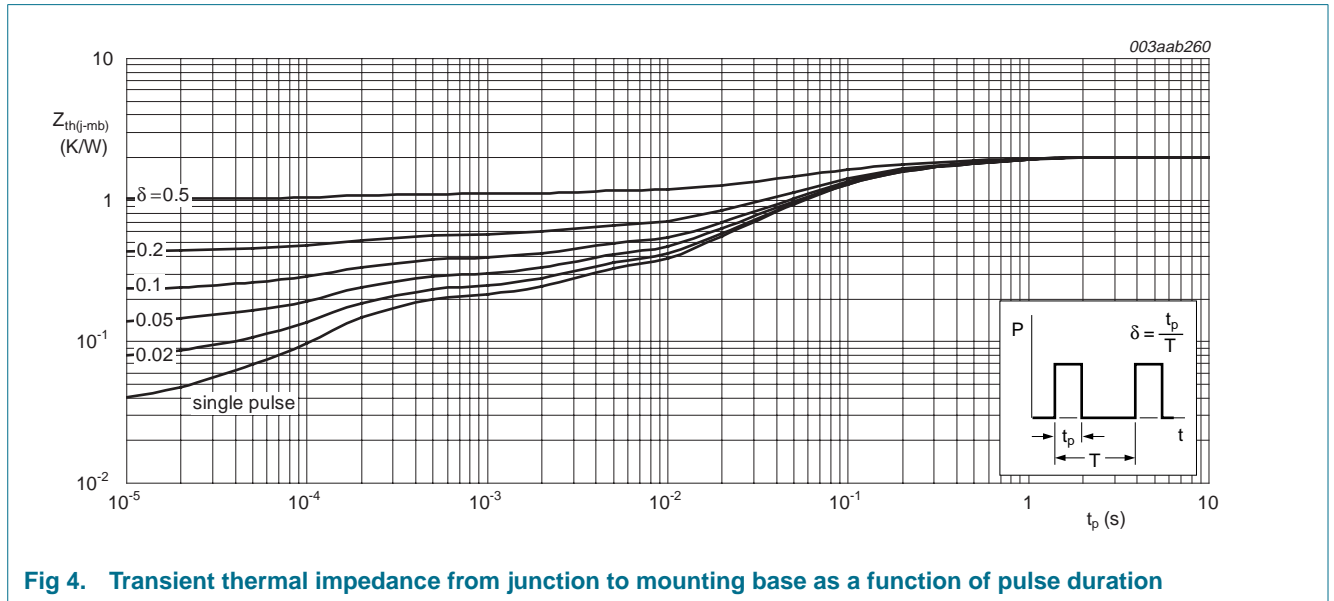
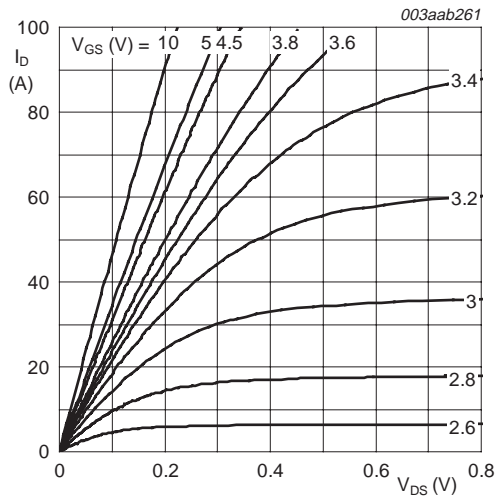


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

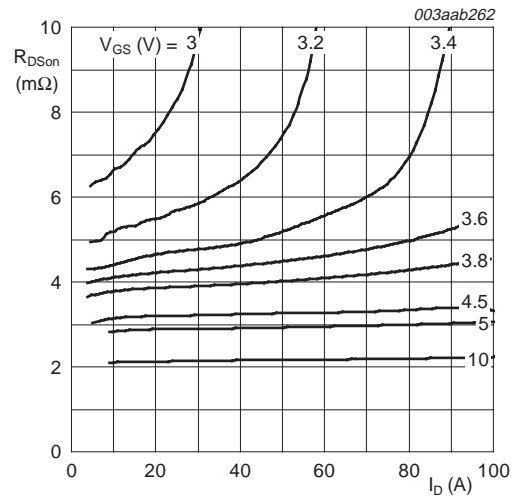
Table 5: Characteristics
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V T _j = 25 °C	30	-	-	V
		T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; see Figure 9 and 10 T _j = 25 °C	1.3	1.7	2.15	V
		T _j = 150 °C	0.8	-	-	V
		T _j = -55 °C	-	-	2.6	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V T _j = 25 °C	-	-	1	μA
		T _j = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = ±16 V; V _{DS} = 0 V	-	-	100	nA
R _G	gate resistance	f = 1 MHz	-	0.7	-	Ω
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; see Figure 6 and 8 T _j = 25 °C	-	2.3	3.3	mΩ
		T _j = 150 °C	-	4.1	6	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; see Figure 6 and 8	-	3.4	4.5	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 12 V; V _{GS} = 4.5 V; see Figure 11 and 12	-	30.5	-	nC
Q _{GS}	gate-source charge		-	15.4	-	nC
Q _{GS1}	pre-V _{GS(th)} gate-source charge		-	7.7	-	nC
Q _{GS2}	post-V _{GS(th)} gate-source charge		-	7.7	-	nC
Q _{GD}	gate-drain charge		-	6.9	-	nC
V _{GS(pl)}	gate-source plateau voltage		-	3.4	-	V
Q _{G(tot)}	total gate charge	I _D = 0 A; V _{DS} = 0 V; V _{GS} = 4.5 V	-	28.5	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 12 V; f = 1 MHz; see Figure 14	-	4840	-	pF
C _{oss}	output capacitance		-	960	-	pF
C _{rss}	reverse transfer capacitance		-	410	-	pF
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 0 V; f = 1 MHz	-	5380	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 12 V; R _L = 0.5 Ω; V _{GS} = 4.5 V;	-	41	-	ns
t _r	rise time	R _G = 5.6 Ω	-	75	-	ns
t _{d(off)}	turn-off delay time		-	52	-	ns
t _f	fall time		-	27	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; see Figure 13	-	0.82	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V	-	52	-	ns
Q _r	recovered charge		-	23	-	nC



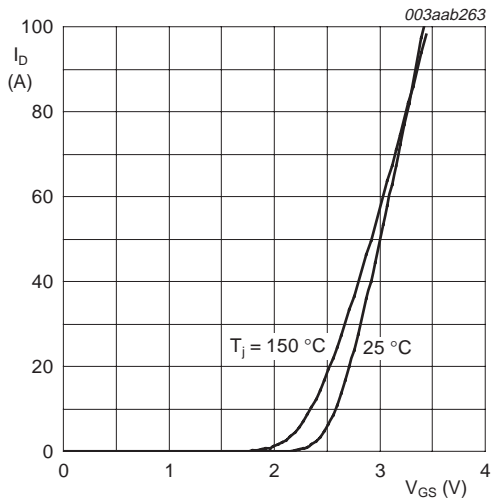
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



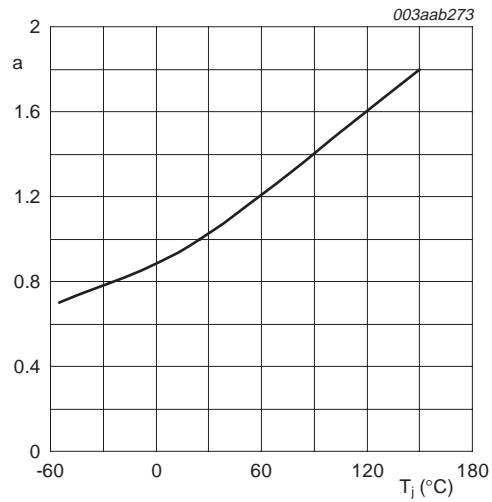
$T_j = 25\text{ }^\circ\text{C}$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



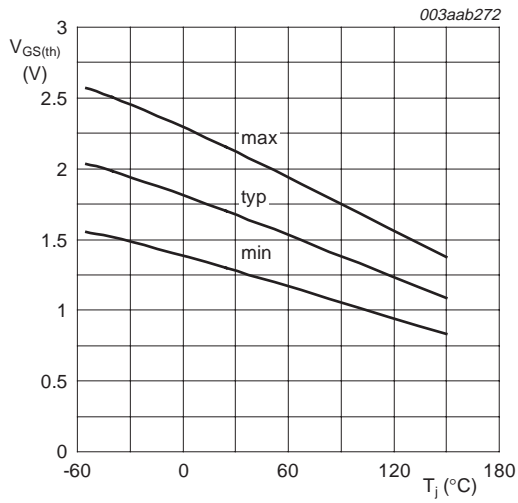
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DS(on)}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



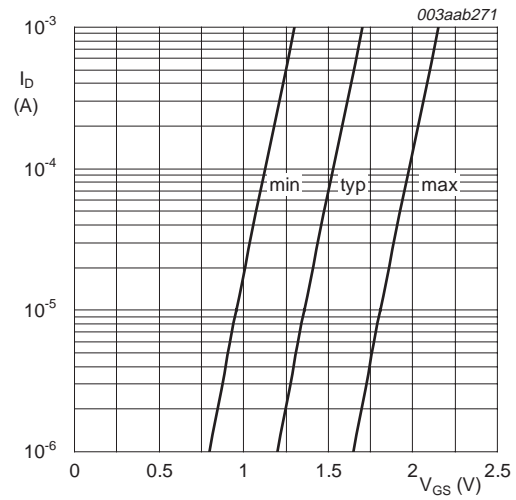
$$a = \frac{R_{DS(on)}}{R_{DS(on)(25\text{ }^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



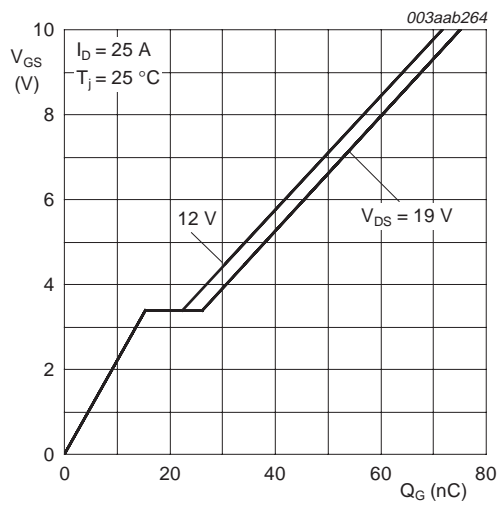
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



$T_j = 25 \text{ }^{\circ}C; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V and } 19 \text{ V}$

Fig 11. Gate-source voltage as a function of gate charge; typical values

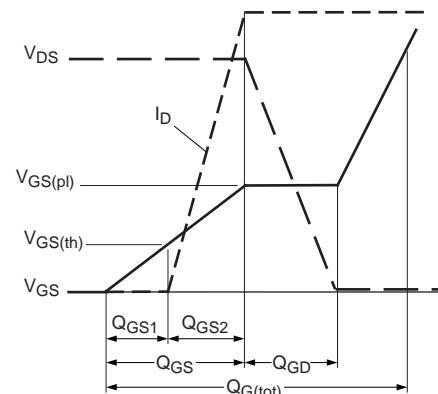
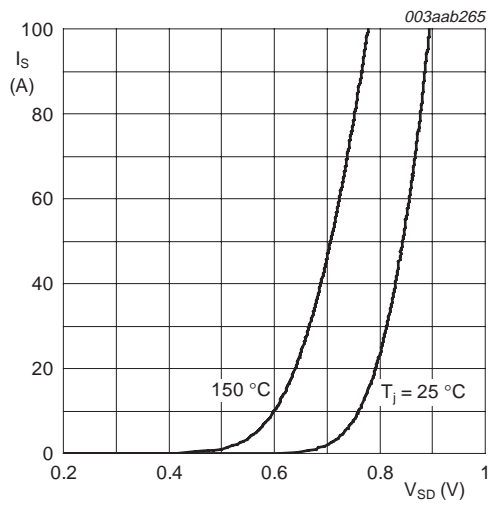
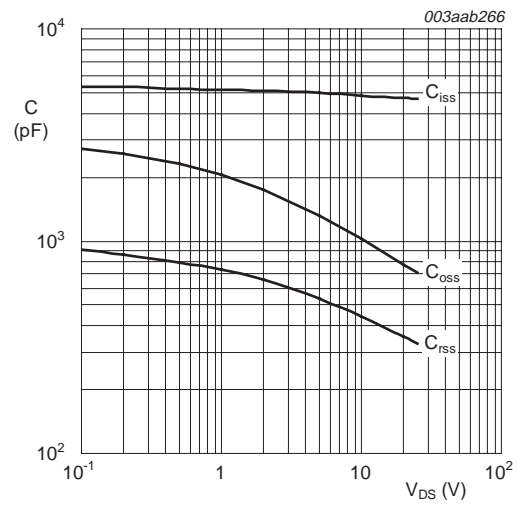


Fig 12. Gate charge waveform definitions



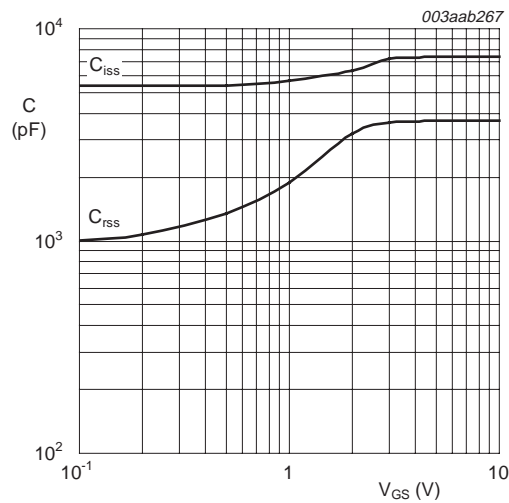
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{GS} = 0\text{ V}$

Fig 13. Source current as a function of source-drain voltage; typical values



$V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{DS} = 0\text{ V}$; $f = 1\text{ MHz}$

Fig 15. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

7. Package outline

Plastic single-ended surface mounted package (LPAK); 4 leads

SOT669

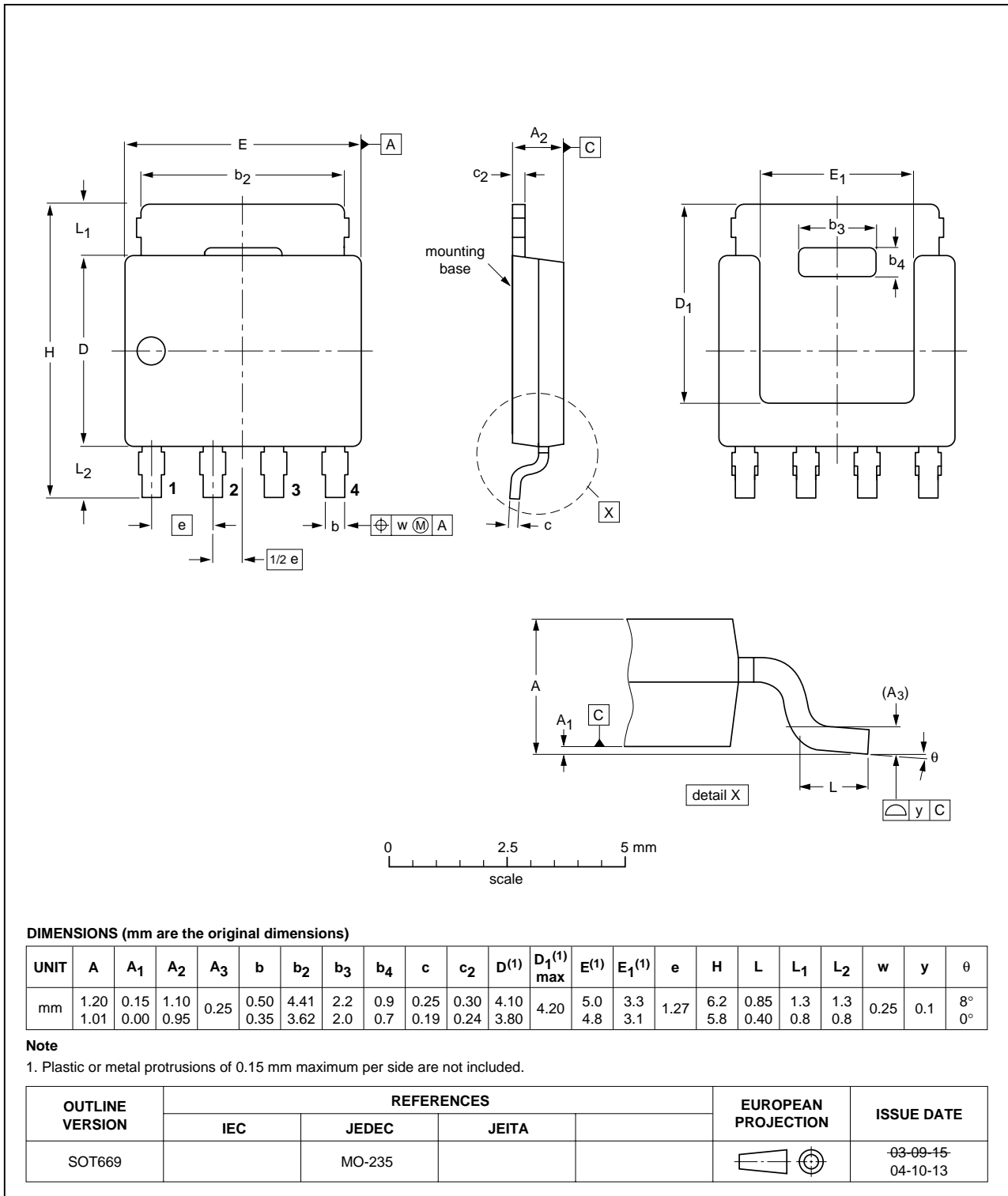


Fig 16. Package outline SOT669 (LPAK)

8. Revision history

Table 6: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PH3330L_1	20060201	Product data sheet	-	-	-

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Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
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